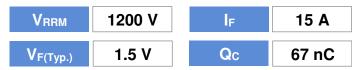


Silicon Carbide Schottky Barrier Diode



Features

- Temperature Independent Switching Behavior
- High Surge Current Capability
- Positive Temperature Coefficient on VF
- Low Conduction Loss
- Zero Reverse Recovery
- High junction temperature 175 °C
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

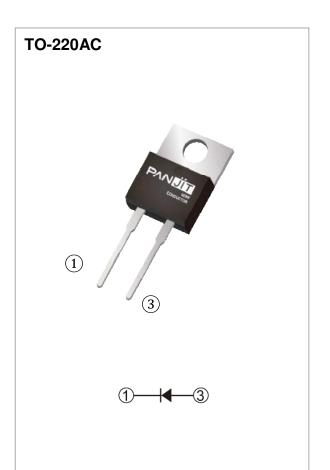
- Case: TO-220AC molded plastic
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.067 ounces, 1.89 grams

Application

• PFC, UPS, PV Inverter, EV Charging Station, Welder

Maximum Ratings and Thermal Characteristics (Tc = 25 °C unless otherwise specified)

PARAMETE	SYMBOL	LIMIT	UNITS		
Repetitive Peak Reverse Voltage	V _{RRM}	1200	V		
DC Blocking Voltage	V _{DC}	1200	V		
Continuous Forward Current	Tc= 155 °C	IF	15	А	
Repetitive Peak Surge Current	$T_{C}= 25 \circ C$, $t_{p}=10ms$		60	А	
Half Sine Wave, D=0.1	$T_C=125 \circ C$, $t_p=10ms$	IFRM	48		
Peak Forward Surge Current	$T_{C}=25 \circ C$, $t_{p}=10ms$		120	А	
Half Sine Wave	$T_C=125 \circ C$, $t_p=10ms$		104		
Peak Forward Surge Current $t_p = 10us, Pulse$	IFSM	880	А		
Maximum Power Dissipation	P _{total}	223.9	W		
Operating Junction Temperature Ra	TJ	-55~175	٥C		
Storage Temperature Range	Tstg	-55~175	°C		





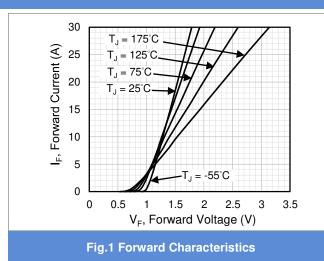
Electrical Characteristics ($T_c = 25$ °C unless otherwise specified)

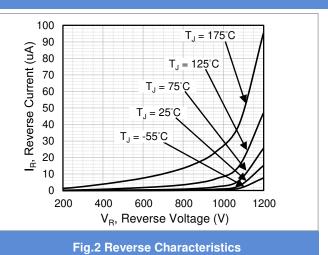
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Forward Voltage Drop	VF	I _F = 15 A, T _J = 25 °C	-	1.5	1.7	V	
		I _F = 15 A, T _J = 175 °C	-	2.0	-		
Reverse Leakage Current	I _R	$V_{R} = 1200 V, T_{J} = 25 ^{\circ}C$	-	15	140	μA	
		V _R = 1200 V, T _J = 175 °C	-	0.1	-	mA	
Total Capacitive Charge	Qc	I _F = 15 A, V _R = 800V	-	67	-	nC	
Total Capacitance	С	$V_R = 1V$, f = 1MHz	-	815	-	pF	
		V _R = 400V, f = 1MHz	-	59.5	-	pF	
		V _R = 800V, f = 1MHz	-	45.9	-	pF	
Capacitance Stored Energy	Ec	V _R = 800V	-	20	-	μJ	
Thermal Resistance	Rejc		-	0.67	-	°C/W	

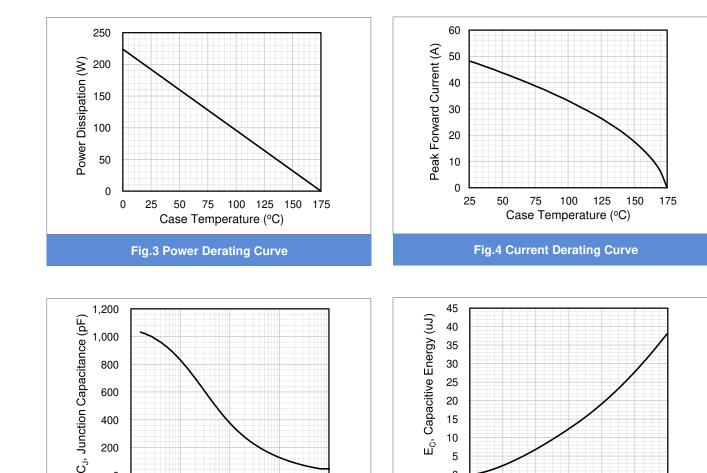


PCDP15120G1









V_R, Reverse Bias Voltage (V)

Fig.5 Typical Junction Capacitance

0.1

V_B, Reverse Bias Voltage (V)

Fig.6 Capacitance Stored Energy

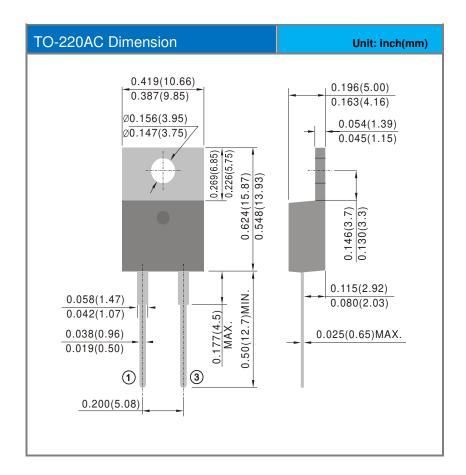
800 1000



Product and Packing Information

Part No. Package Type		Packing Type	Marking	
PCDP15120G1	TO-220AC	50pcs / Tube	CDP15120G1	

Packaging Information





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